



Temperature independent low firing $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($0.2 \leq x \leq 0.8$) microwave dielectric ceramics



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ABSTRACT

A scheelite structured $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($0.2 \leq x \leq 0.8$) ceramics were prepared via solid state reaction method. All the ceramics can be well densified below 780°C . As x value increased from 0.2 to 0.8, microwave dielectric permittivity increased from 14.0 to 27.8, Q_f ($Q = \text{quality factor} = 1/\text{dielectric loss}$; $f = \text{resonant frequency}$) value decreased from 42,000 GHz to 19,000 GHz, and TCF shifted from $-50 \text{ ppm}/^\circ\text{C}$ to $+18 \text{ ppm}/^\circ\text{C}$. The best microwave dielectric properties with permittivity between 23.54 and 23.56, Q_f value between 24,000 GHz–21,000 GHz and TCF value $\sim -8 \text{ ppm}/^\circ\text{C}$ in wide temperature range 25°C – 130°C were obtained in $x = 0.6$ ceramic. This work showed that Bi played an important role to modify the TCF from negative to positive value in scheelite materials and this result further accelerate the application of scheelite materials in low temperature co-fired ceramics (LTCC) technology.

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1. Introduction

Microwave dielectric ceramics have played important roles in dielectric resonator, filter and substrate. Search for novel materials with high quality factor Q (low dielectric loss), low sintering temperature with co-sinterable metal electrode are current two hot topics microwave dielectric ceramics due to the fast development of low temperature co-fired ceramics (LTCC) technology, which is a very popular fabrication method in modern electronic devices [1–6]. Most commercial microwave dielectric ceramics with high Q_f value ($Q = 1/\text{dielectric loss}$; $f = \text{resonant frequency}$) belong to the famous ABO_3 perovskite structure [7–9]. However, it is quite difficult to lower the sintering temperatures of ABO_3 perovskite ceramics to below the melting point (961°C) of most common metal electrode silver in LTCC technology without serious deterioration in Q_f values. Recently, another large family called scheelite has attracted much attention due to the adaptability of this structure, high Q_f value and adjustable temperature coefficient of resonant frequency (TCF) value [10–13]. Hong et al. [10,11] first reported the microwave dielectric properties of AWO_4 and AMoO_4

($A = \text{Ca, Sr, Ba}$) ceramics and they show low permittivity (8–17), high Q_f values (32,000–69,000 GHz), and negative TCF values (-53 to $-78 \text{ ppm}/^\circ\text{C}$). Although this system possesses high Q_f value, their TCF value are all large negative. Subsequently, another alkali metal bismuth molybdates system $(\text{ABi})_{1/2}\text{MoO}_4$ ($A = \text{Li, Na, K, Rb, Ag}$) with scheelite and scheelite related structures were also reported to possess good microwave dielectric properties and some of them show positive TCF value [14–16]. Among them, $(\text{LiBi})_{1/2}\text{MoO}_4$ possesses an ultralow sintering temperature $\sim 560^\circ\text{C}$, the largest permittivity ~ 41.7 (at 5.5 GHz), the largest positive TCF value $\sim +240 \text{ ppm}/^\circ\text{C}$ but a poor Q_f value $\sim 3200 \text{ GHz}$ [14]. The $(\text{LiBi})_{1/2}\text{MoO}_4$ was found to form solid solution with CaMoO_4 in the full composition range and near zero TCF value was achieved in the $[(\text{Li}_{0.5}\text{Bi}_{0.5})_{0.15}\text{Ca}_{0.85}]\text{MoO}_4$ ceramic with a relative permittivity ~ 14.1 , a Q_f value $\sim 24,000 \text{ GHz}$ (at 10.0 GHz) [17]. Except for $(\text{LiBi})_{1/2}\text{MoO}_4$, $(\text{NaBi})_{1/2}\text{MoO}_4$ and $(\text{AgBi})_{1/2}\text{MoO}_4$ are the only two scheelite compounds that have been reported to possess positive TCF value by now [15]. The $(\text{NaBi})_{1/2}\text{MoO}_4$ was also used to compensate the TCF value of CaMoO_4 ceramic and a temperature stable $(\text{Na}_{0.5}\text{Bi}_{0.5})_{0.6}\text{Ca}_{0.4}\text{MoO}_4$ microwave ceramic with a permittivity ~ 21.9 and a Q_f value $\sim 20,660 \text{ GHz}$ was achieved [18]. Compared with both $(\text{LiBi})_{1/2}\text{MoO}_4$ and $(\text{AgBi})_{1/2}\text{MoO}_4$, $(\text{NaBi})_{1/2}\text{MoO}_4$ possesses higher Q_f value and low cost ingredients, and

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worked well to compensate negative TCF in many other scheelite phases, such as $(\text{Na}_{0.5}\text{La}_{0.5})\text{MoO}_4$ and $(\text{Na}_{0.5}\text{Bi}_{0.5})\text{WO}_4$ etc. [19,20] As well known, scheelite structure is quite adaptable and as large as 1/3 defect can be allowed on the A site as reported in $(\Phi_{1/3}\text{La}_{2/3})\text{MoO}_4$ ceramic [21–23]. In our previous work, it was also found that A site defect can be used to modify the TCF values [24,25]. Besides, heavy Bi^{3+} was found to accelerate shifting TCF value from negative to positive in many systems [26,27]. Hence, in the present work, the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($0.2 \leq x \leq 0.8$) ceramics were prepared via solid state reaction method. The sintering behavior and microwave dielectric properties were studied in detail.

2. Experimental section

Proportionate amounts of reagent-grade starting materials of Bi_2O_3 (>99%, Shu-Du Powders Co. Ltd., Chengdu, China), CaCO_3 , Nd_2O_3 (>99%, Sinopharm Chemical Reagent Co., Ltd, Shanghai, China) and MoO_3 (>99%, Fuchen Chemical Reagents, Tianjin, China) were measured according to the stoichiometric formulation $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($0.2 \leq x \leq 0.8$). Ceramic samples were prepared via the traditional solid state reaction method as described in our previous work [2,15]. The calcination temperature is 600°C and the samples were sintered under air atmosphere in $660\text{--}780^\circ\text{C}$. Room temperature X-ray diffraction (XRD) was performed using a XRD with $\text{Cu K}\alpha$ radiation (Rigaku D/MAX-2400 X-ray diffractometry, Tokyo, Japan). Prior to examination sintered pellets were crushed in a mortar and pestle to powder. Diffraction pattern was obtained between 2θ of $5\text{--}65^\circ$ for phase identification

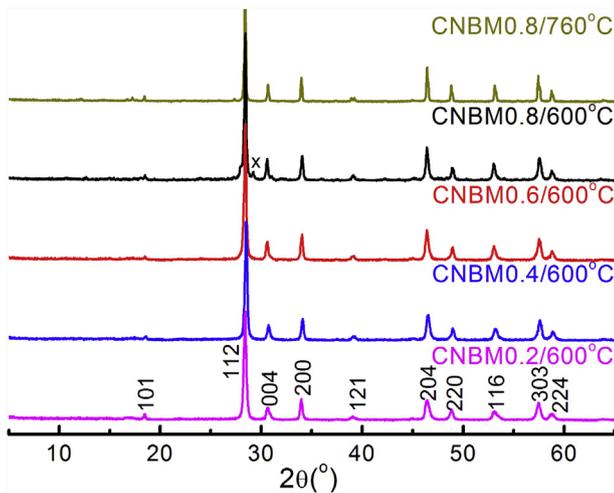


Fig. 1. XRD patterns of the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($x = 0.2, 0.4, 0.6$ and 0.8) ceramics calcined at 600°C and sintered at 760°C for $x = 0.2$.

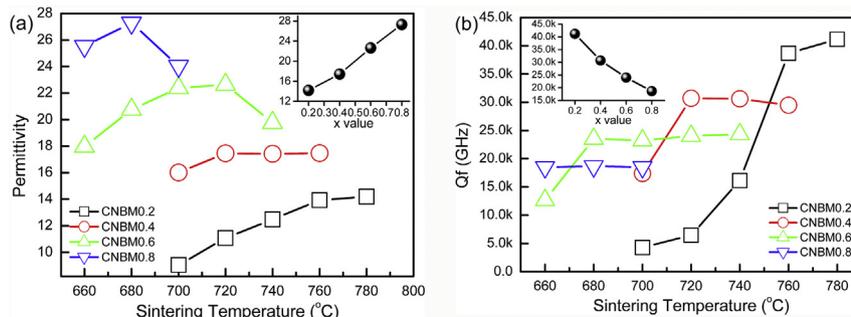


Fig. 2. Microwave dielectric permittivity (a) and Qf value of the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($x = 0.2, 0.4, 0.6$ and 0.8) ceramics as a function of sintering temperature.

at a step size of 0.02° . Dielectric properties at microwave frequency were measured with the $\text{TE}_{01\delta}$ dielectric resonator method with a network analyzer (HP 8720 Network Analyzer, Hewlett-Packard) and a temperature chamber (Delta 9023, Delta Design, Poway, CA). The temperature coefficient of resonant frequency TCF (τ_f) was calculated with the following formula:

$$\text{TCF}(\tau_f) = \frac{f_T - f_{T_0}}{f_{T_0} \times (T - T_0)} \times 10^6 \quad (1)$$

where the f_T and f_{T_0} were the $\text{TE}_{01\delta}$ resonant frequencies at temperature T and T_0 , respectively.

3. Results and discussions

XRD patterns of the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($x = 0.2, 0.4, 0.6$ and 0.8) ceramics calcined at 600°C and sintered at 760°C for $x = 0.2$ are shown in Fig. 1. Single scheelite phases were formed in almost all the compositions except for $x = 0.8$ after calcinations at 600°C . The intensity of XRD of secondary phases in $x = 0.8$ sample are quite weak and it might be Nd_2MoO_6 or $\text{Bi}_2\text{Mo}_3\text{O}_{12}$ or both. After being well sintered at 680°C , the secondary phases disappeared and pure scheelite phase was formed. Although 25 mol. % defects were introduced on the A site, scheelite phase can also be kept in the full composition range here and it is very adaptable.

Microwave dielectric permittivity and Qf value of the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($x = 0.2, 0.4, 0.6$ and 0.8) ceramics as a function of sintering temperature are shown in Fig. 2. As sintering temperature increased, permittivity of the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ceramics increased first and then reached their separate saturated values. Qf values also showed similar trend and also good stability in wide sintering temperature ranges. As the x value increased from 0.2 to 0.8, sintering temperature decreased gradually from 780°C to 680°C due to the increase in Bi content (melting points of Bi_2O_3 is $817^\circ\text{C} \ll 2233^\circ\text{C}$ for Nd_2O_3). Meanwhile, microwave permittivity increased from about 14 to 27.8 and Qf value decreased from 42,000 GHz to 19,000 GHz and this might be attributed to the larger ionic polarizability of Bi^{3+} (6.12 \AA^3) than that of Nd^{3+} (5.01 \AA^3) as reported by Shannon [28]. Dielectric polarizations at microwave region are commonly contributed from the ionic and electronic displacive polarizations, in which the latter's contribution can be ignored in high k materials. A classic damped oscillator model can be employed to describe the relative displacement of cations and anions, from which an inversely proportional relation between the Qf and ϵ_r can be deduced as the following [17,29].

$$Q \times f \approx \frac{(ze)^2 / mV\epsilon_0}{2\pi\gamma \times (\epsilon'(\omega) - \epsilon(\infty))} \quad (2)$$

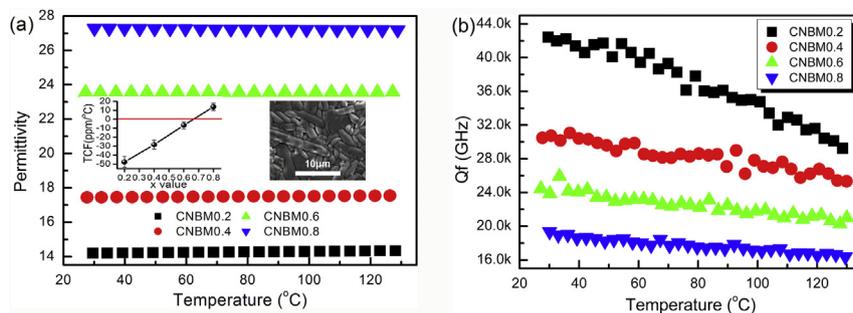


Fig. 3. Temperature dependence of microwave dielectric permittivity (a) and Qf value (b) of the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($x = 0.2, 0.4, 0.6$ and 0.8) ceramics (inset is the thermal etched surface of $x = 0.6$ sample sintered at 720°C).

This relation can well explain the relation between x value, permittivity and Qf values of the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ solid solution system.

Temperature dependence of microwave dielectric permittivity, Qf value and the TCF values of the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($x = 0.2, 0.4, 0.6$ and 0.8) ceramics are shown in Fig. 3. As shown in the inset of Fig. 3a, TCF values shifted linearly from -50 ppm/ $^\circ\text{C}$ for $x = 0.2$ sample to $+18$ ppm/ $^\circ\text{C}$ for $x = 0.8$ sample. TCF value gives the temperature dependence of resonant frequency and it is mainly determined by the temperature dependence of permittivity. As shown in Fig. 3a, permittivity of the $x = 0.6$ sample increased slightly from 23.54 to 23.56 as temperature changed from 25°C to 130°C and shows quite good temperature independency. Different from the large drop in Qf value for $x = 0.2$ sample as temperature increased, the Qf value of $x = 0.6$ ceramic decreased slightly from 24,000 GHz at 25°C to 21,000 GHz at 130°C , which means this ceramic is quite isolating and shows quite low dielectric loss in wide temperature range. Also, the $x = 0.6$ ceramic sintered at 720°C shows quite dense microstructure as seen from the inset in Fig. 3a, which indicates that Bi substitution for Nd remarkably lowered the densification temperatures of the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ceramics.

4. Conclusions

A scheelite solid solution with 25 mol. % defect on A site was formed in the $[\text{Ca}_{0.25}(\text{Nd}_{1-x}\text{Bi}_x)_{0.5}]\text{MoO}_4$ ($x = 0.2, 0.4, 0.6$ and 0.8) ceramics. All the ceramics can be well densified below 780°C . As the increase of Bi content in this system, TCF value can be easily modified from negative to positive values. Temperature stable microwave dielectric properties can be obtained in $x = 0.6$ sample with permittivity about 23.54–23.56 and Qf value between 24,000 GHz–21,000 GHz in wide temperature range 25°C – 130°C and this system might be good candidate for LTCC technology.

Declarations of interest

None.

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